



**THE DATASHEET OF  
BT155K-1200TQ**



## 1. General description

Planar passivated Silicon Controlled Rectifier in a SOT1259 (3-lead TO-3P) plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

## 2. Features and benefits

- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- High voltage capacity
- Very high current surge capability

## 3. Applications

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- Traction battery charging

## 4. Quick reference data

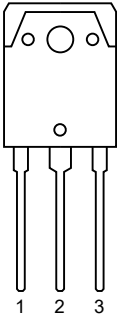

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	1200	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	1200	V
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	650	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	-	715	A
$T_j$	junction temperature		-	-	150	°C
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 131\text{ °C}$	-	-	50	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 131\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	79	A

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a> ; <a href="#">Fig. 8</a>	-	-	50	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 800\text{ V}$ ; $T_j = 125\text{ °C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	1500	-	-	V/ $\mu$ s

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>TO3P (SOT1259)</p>	 <p>sym037</p>
2	A	anode		
3	G	gate		
mb	mb	mounting base; connected to anode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT155K-1200T	TO3P	Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO3P	SOT1259

## 7. Marking

Table 4. Marking codes

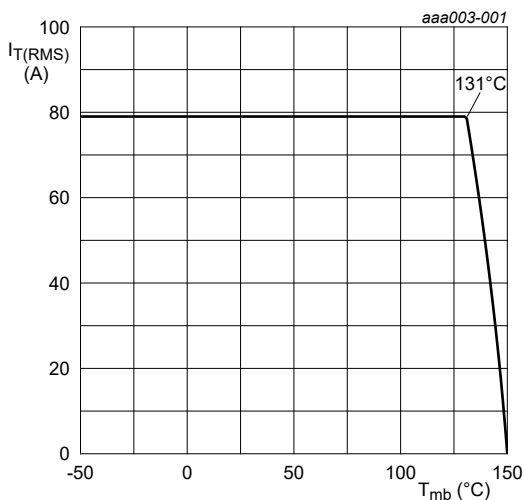
Type number	Marking code
BT155K-1200T	BT155K-1200T

## 8. Limiting values

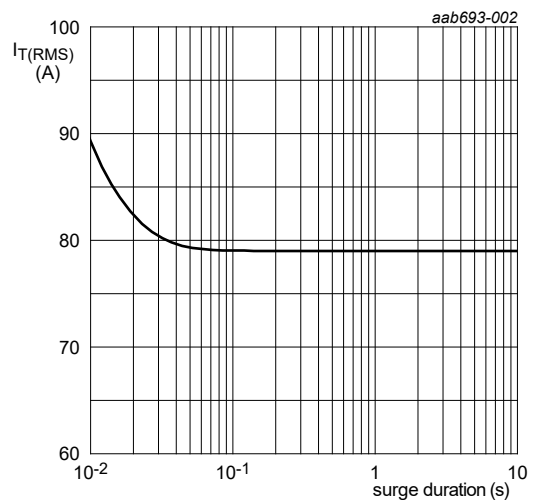
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	1200	V
$V_{RRM}$	repetitive peak reverse voltage		-	1200	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 131\text{ °C}$	-	50	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 131\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	79	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	650	A
		half sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	715	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	2113	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 200\text{ mA}$	-	150	A/ $\mu$ s
$I_{GM}$	peak gate current		-	8	A
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	150	°C



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 131\text{ °C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

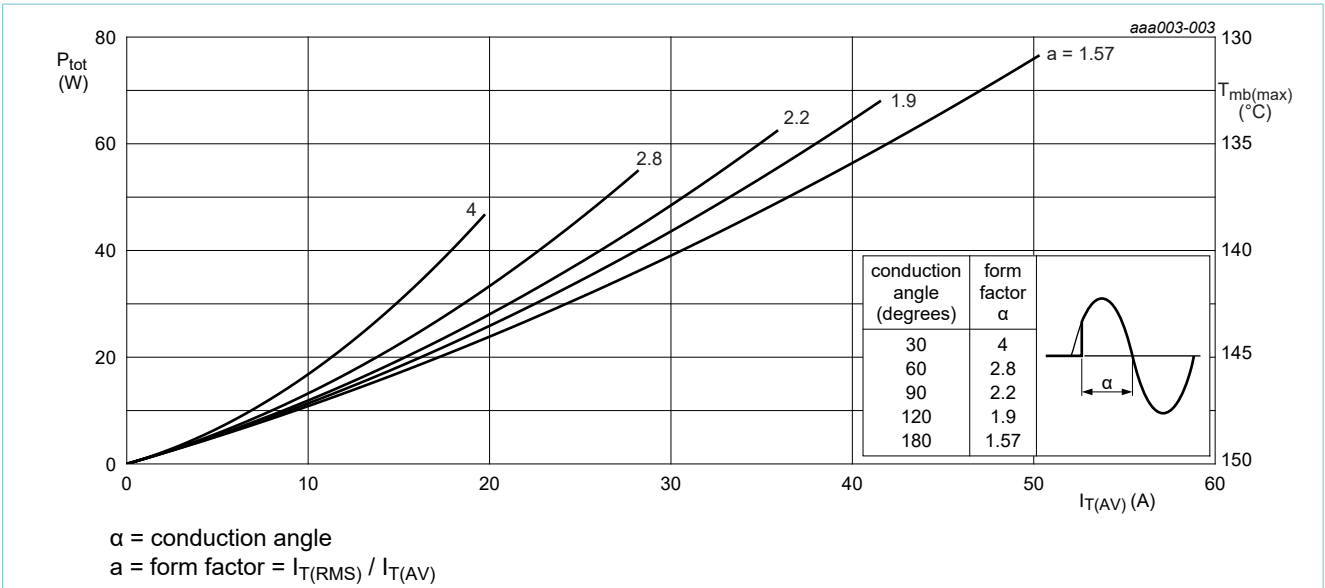


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

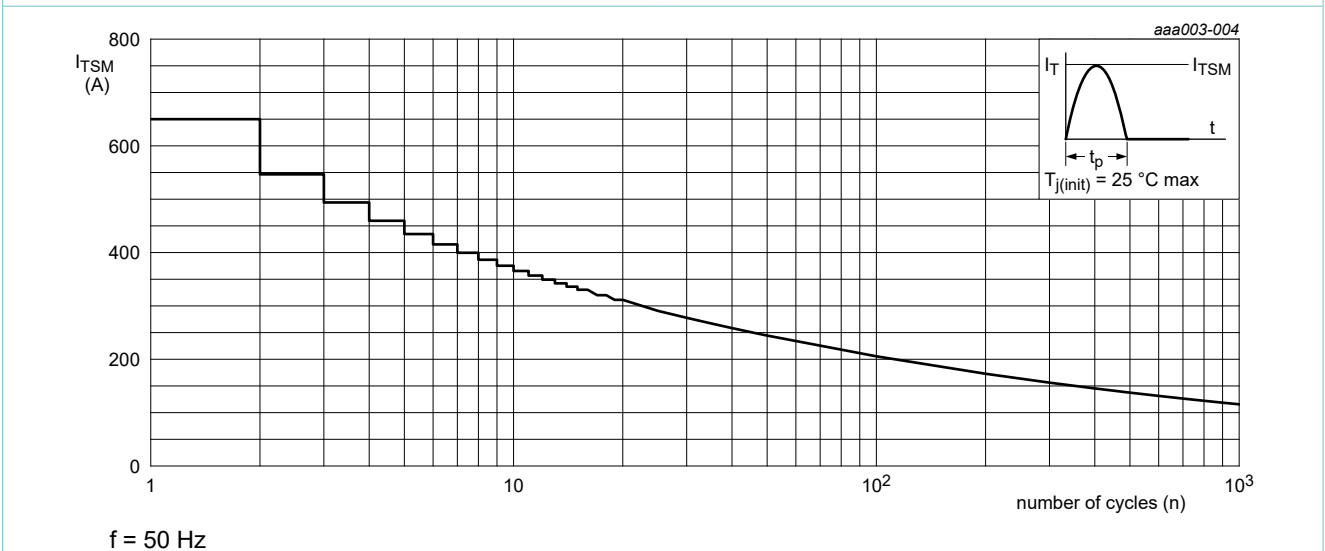
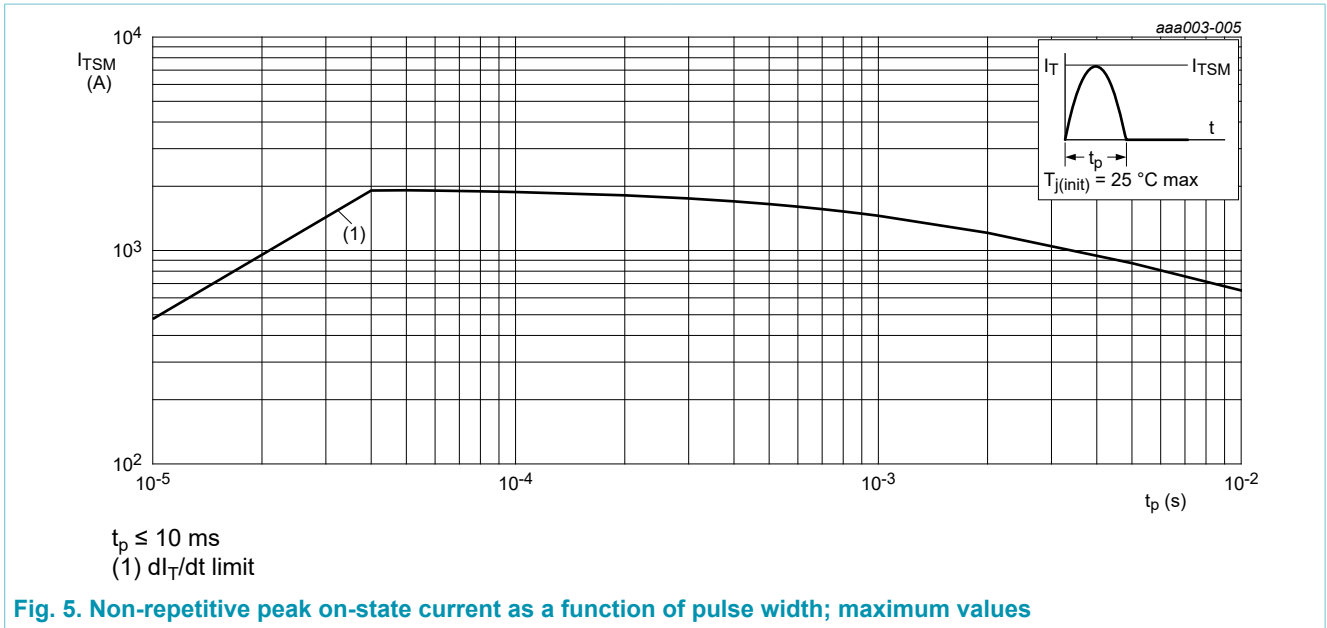


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 6</a>	-	-	0.25	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

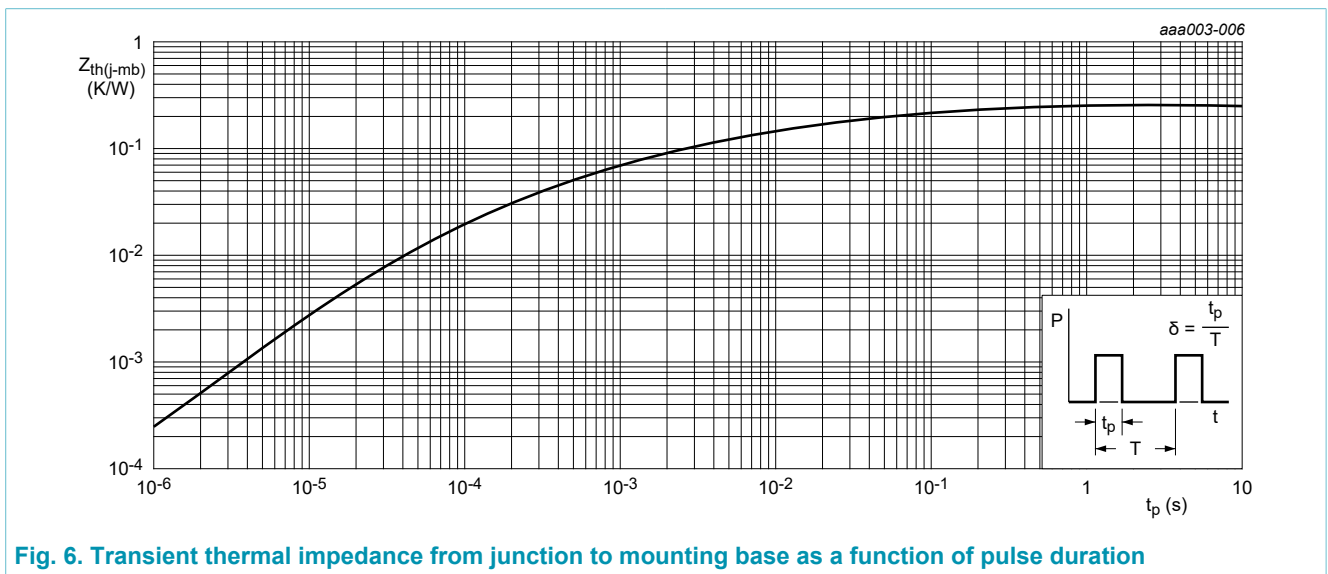


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> ; <a href="#">Fig. 8</a>	-	-	50	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	300	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	-	200	mA
$V_T$	on-state voltage	$I_T = 50\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	1.3	V
		$I_T = 90\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	-	0.7	1	V
		$V_D = 800\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 1200\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	-	3	mA
$I_R$	reverse current	$V_R = 1200\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	-	3	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	1500	-	-	V/ $\mu\text{s}$
		$V_{DM} = 800\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	1000	-	-	V/ $\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ }^\circ\text{C}$	-	2	-	$\mu\text{s}$
$t_q$	commutated turn-off time	$V_{DM} = 804\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{TM} = 20\text{ A}$ ; $V_R = 25\text{ V}$ ; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$ ; $dV_D/dt = 50\text{ V}/\mu\text{s}$ ; $R_{GK(ext)} = 100\text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ )	-	150	-	$\mu\text{s}$

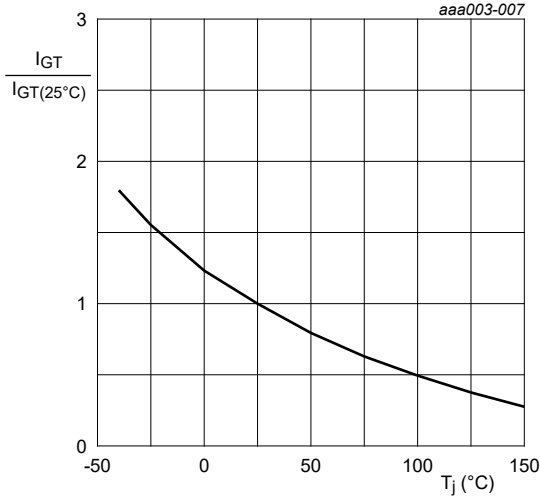


Fig. 7. Normalized gate trigger current as a function of junction temperature

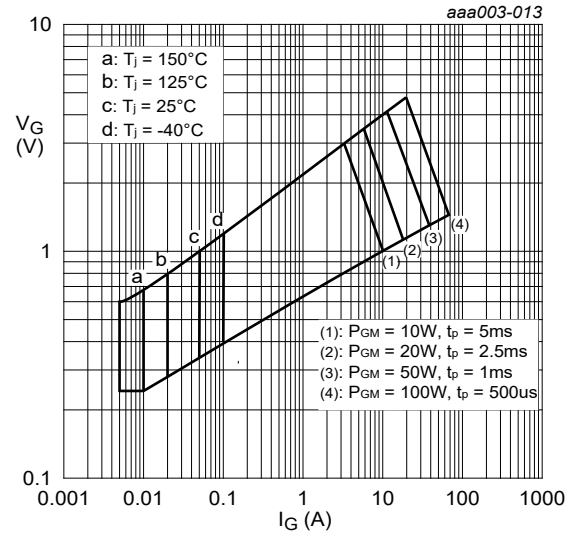


Fig. 8. Gate voltage as a function of gate current

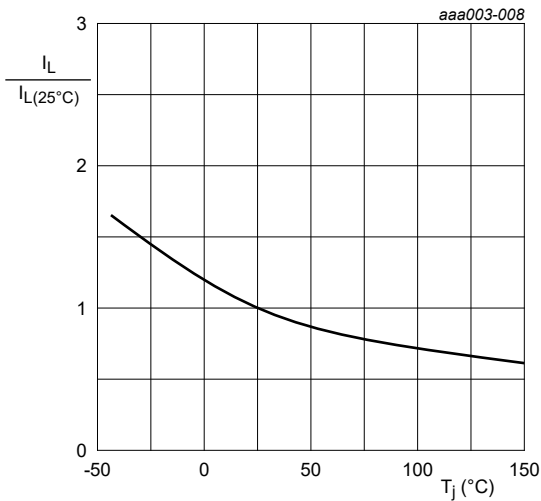


Fig. 9. Normalized latching current as a function of junction temperature

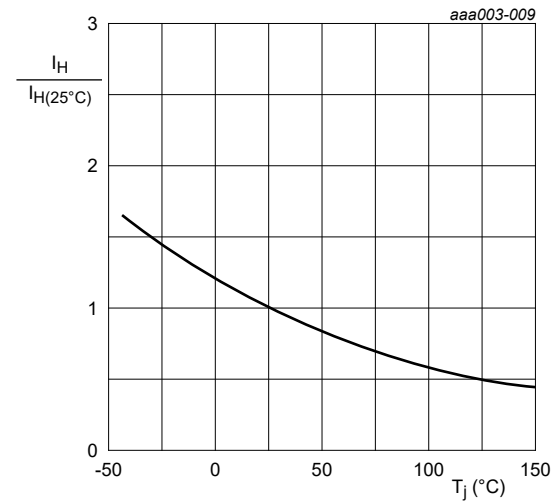
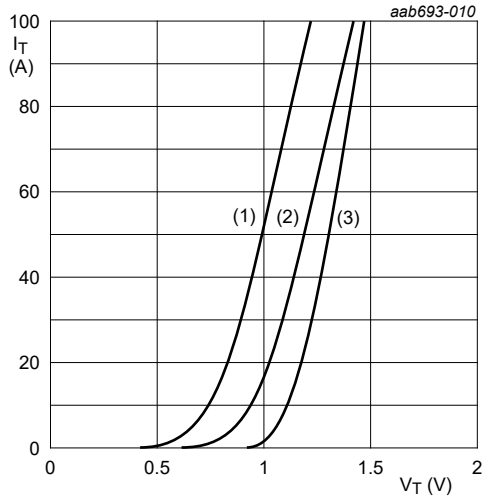
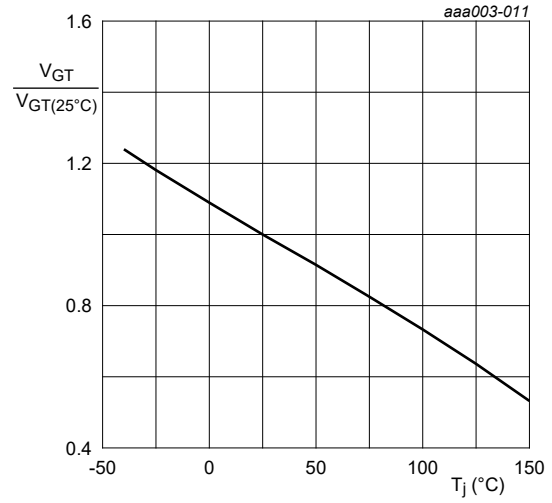


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 0.989\text{ V}; R_s = 0.0042\ \Omega$   
 (1)  $T_j = 150\text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 150\text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25\text{ }^\circ\text{C}$ ; maximum values

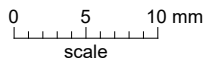
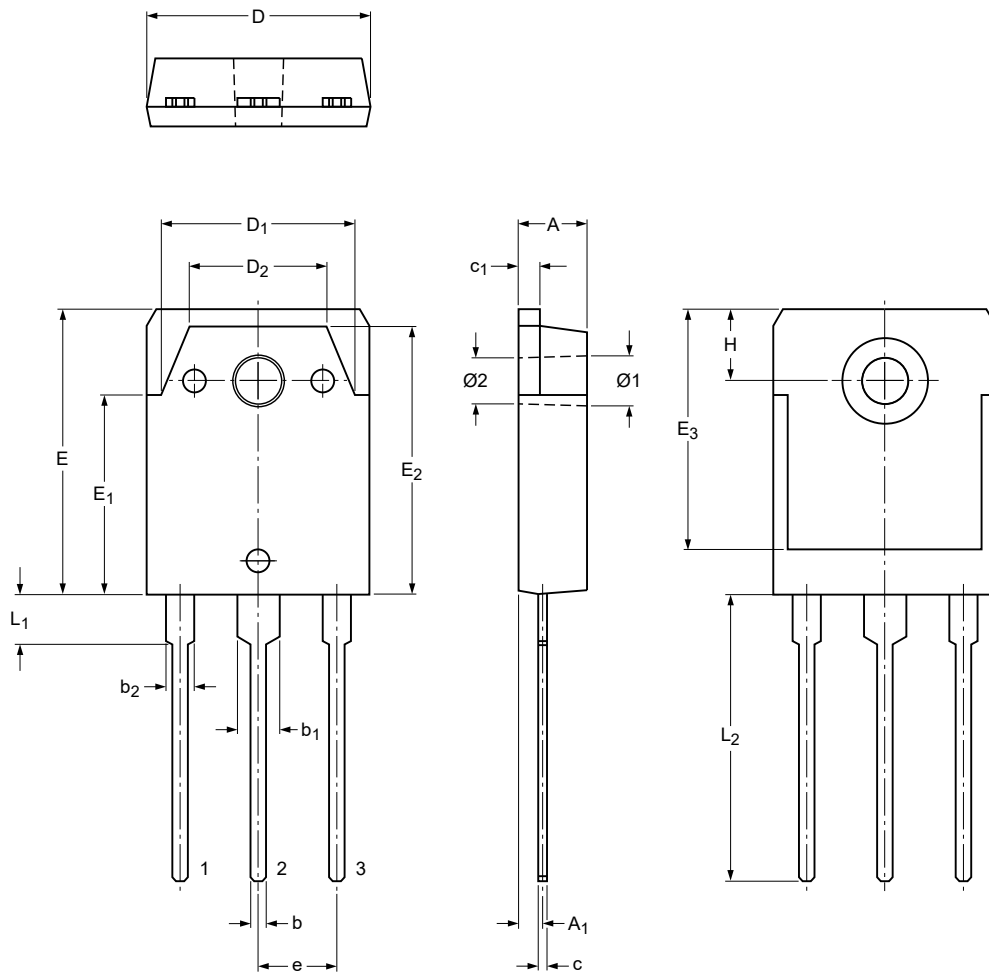
**Fig. 11. On-state current as a function of on-state voltage**



**Fig. 12. Normalized gate trigger voltage as a function of junction temperature**

### 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO3P SOT1259



Dimensions (mm are the original dimensions)

Unit	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	c <sub>1</sub>	D	D <sub>1</sub>	D <sub>2</sub>	e	E	E <sub>1</sub>	E <sub>2</sub>	E <sub>3</sub>	H	L <sub>1</sub>	L <sub>2</sub>	Ø1	Ø2
max	5.0	1.6	1.2	3.2	2.2	0.75	1.65	15.8	13.8	9.8		20.1	14.1	18.9	17.06	5.2	3.7	20.3	3.5	3.3
nom											5.45									
min	4.6	1.2	0.8	2.8	1.8	0.55	1.45	15.4	13.4	9.4	(typ)	19.7	13.7	18.5	16.46	4.8	3.3	19.7	3.3	3.1

sot1259\_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT1259	TO3P				14-10-21- 14-10-22

Fig. 13. Package outline TO3P (SOT1259)

## 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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